Product data sheet

1. General description

Enhanced ultrafast power diode in a SOD59 (2-lead TO-220AC) plastic package.

2. Features and benefits

- · High thermal cycling performance
- Low thermal resistance
- Low on-state losses
- · Soft recovery characteristic

3. Applications

- Dual Mode (DCM and CCM) PFC
- · Power Factor Correction (PFC) for Interleaved Topology

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	meter Conditions		Values			Unit	
Absolute maximum rating								
V_{RRM}	repetitive peak reverse voltage		600				V	
$I_{F(AV)}$	average forward current	$δ = 0.5$; square-wave pulse; $T_{mb} \le 126$ °C; Fig. 1; Fig. 2		5			А	
I _{FRM}	repetitive peak forward current	δ = 0.5 ; t_p = 25 μs; T_{mb} ≤ 126 °C; square-wave pulse	10			А		
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 3			А			
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 3			А			
Symbol	Parameter	Conditions	Min Typ Max		Unit			
Static ch	Static characteristics							
V _F	forward voltage	I _F = 5 A; T _j = 25 °C; <u>Fig. 5</u>		-	1.3	1.9	V	
		I _F = 5 A; T _j = 150 °C; <u>Fig. 5</u>		-	1.1	1.7	V	
Dynamic	characteristics							
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 6$		-	17.5	35	ns	

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BYV25F-600

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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode	mb	
2	А	anode	7 7	K — A 001aaa020
mb	К	mounting base; cathode	1 2 TO-220AC (SOD59)	001aaa020

6. Ordering information

Table 3. Ordering information

Type number	r Package		
	Name	Description	Version
BYV25F-600 TO-220AC		plastic single-ended package; heatsink mounted; 1 mounting hole; 2-lead TO-220AC	SOD59

7. Marking

Table 4. Marking codes

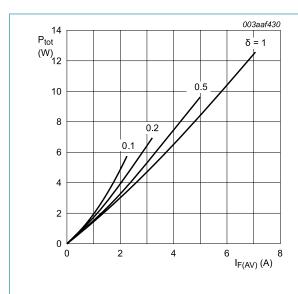
Type number	Marking codes
BYV25F-600	BYV25F-600

8. Limiting values

Table 5. Limiting values

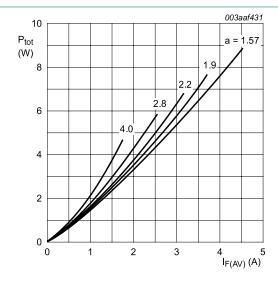
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
V_{RRM}	repetitive peak reverse voltage		600	V
V_{RWM}	crest working reverse voltage		600	V
V_R	reverse voltage	DC	600	V
I _{F(AV)}	average forward current	$δ$ = 0.5 ; square-wave pulse; $T_{mb} \le 126$ °C; Fig. 1; Fig. 2	5	А
I _{FRM}	repetitive peak forward current	δ = 0.5 ; t _p = 25 µs; T _{mb} ≤ 126 °C; square-wave pulse	10	А
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 3	60	А
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 3	66	А
T _{stg}	storage temperature		-40 to 150	°C
T _j	junction temperature		150	°C



$$\begin{split} I_{F(AV)} &= I_{F(RMS)} \times \sqrt{\delta} \\ V_o &= 1.499 \text{ V}; \text{ R}_s = 0.041 \text{ }\Omega \end{split}$$

Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values



a = form factor = $I_{F(RMS)}/I_{F(AV)}$ V_o = 1.499 V; R_s = 0.041 Ω

Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

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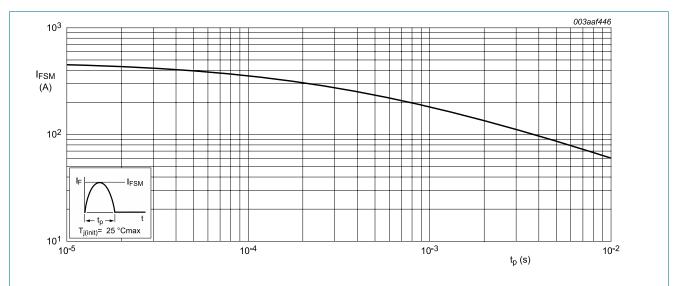


Fig. 3. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values

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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{\text{th(j-mb)}}$	thermal resistance from junction to mounting base	Fig 4	-	-	2.5	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	-	60	-	K/W

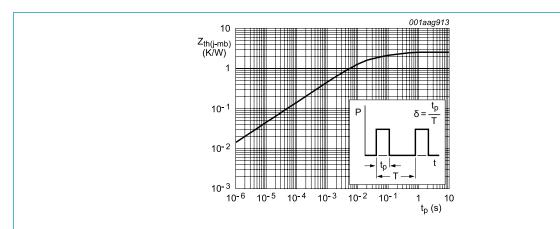


Fig. 4. Transient thermal impedance from junction to mounting base as a function of pulse width

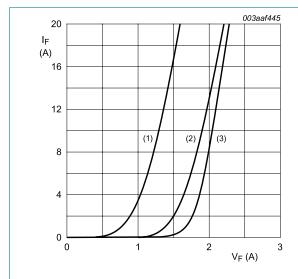
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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
				.,,,,	ax	June
Static cha	racteristics					
V_{F}	forward voltage	$I_F = 5 \text{ A}; T_j = 25 \text{ °C}; Fig. 5$	-	1.3	1.9	V
		I _F = 5 A; T _j = 150 °C; <u>Fig. 5</u>	-	1.1	1.7	V
I_R	reverse current	$V_R = 600 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	-	50	μA
		V _R = 600 V; T _j = 100 °C	-	-	1.5	mA
Dynamic	characteristics					
Q_r	recovered charge	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; \frac{\text{Fig. 6}}{}$	-	13	-	nC
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; \frac{\text{Fig. 6}}{}$	-	17.5	35	ns
I _{RM}	peak reverse recovery current	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 6$	-	1.5	-	А
V _{FRM}	forward recovery voltage	I _F = 1 A; dI _F /dt = 100 A/μs; Τ _i = 25 °C; <u>Fig. 7</u>	-	3.2	-	V



(1) T_j = 150 °C; typical values

(2) T_j = 150 °C; maximum values

(3) $T_j = 25 \,^{\circ}\text{C}$; maximum values $V_o = 1.499 \,\text{V}$; $R_s = 0.041 \,\Omega$



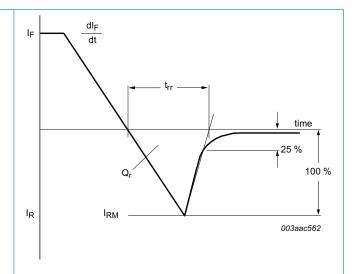
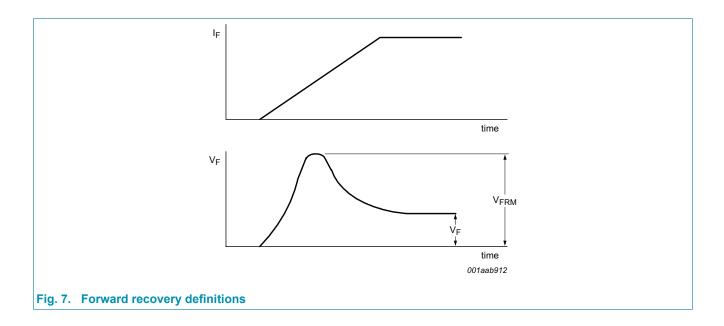
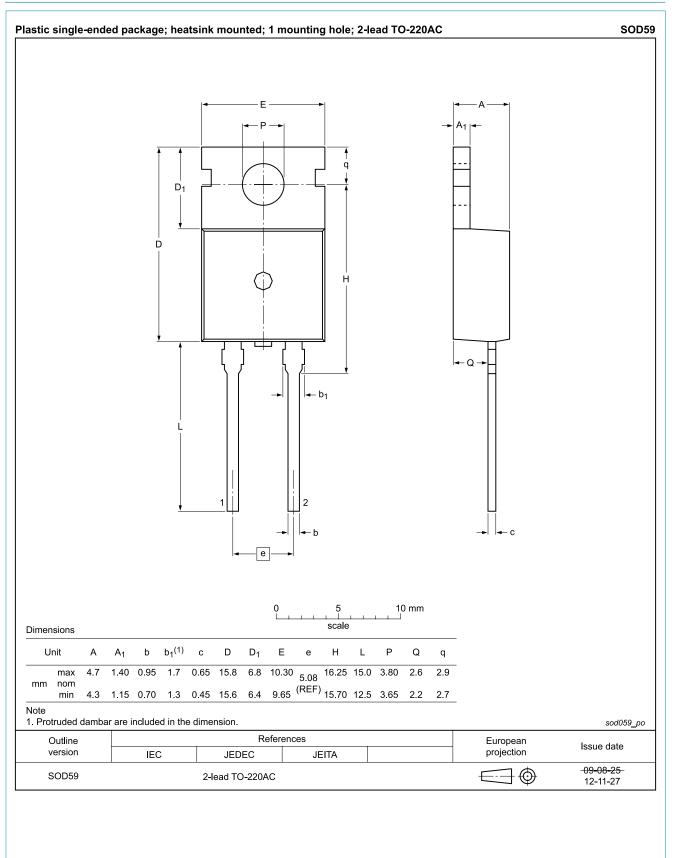


Fig. 6. Reverse recovery definitions; ramp recovery

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11. Package outline



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12. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BYV25F-600 v.3	20180305	Product data sheet	-	BYV25F-600 v.2
Modifications:	Change from NXP version to WeEr	version		
BYV25F-600 v.2	20110307	Product data sheet	-	BYV25F-600 v.1
Modifications:	Various changes to content.			
BYV25F-600 v.1	20101001	Product data sheet	-	-

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13. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions".
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